

THAT WHICH IS CLAIMED IS:

1. A semiconductor image sensor comprising at least one pixel having a photosensing part, characterized in that the photosensing part has a coating which performs a dual function.

2. A sensor as claimed in Claim 1, wherein at least one of the functions of the dual function is a fabrication function.

3. A sensor as claimed in Claim 2, wherein the fabrication function is preventing silicide formation

4. A sensor as claimed in any of Claims 1 to 3, wherein at least one of the functions of the dual function is an in-use function.

5. A sensor as claimed in Claim 4, wherein the in-use function is anti-reflection.

6. A sensor as claimed in any preceding Claim, wherein the photosensing part is a photo-diode.

7. A sensor as claimed in Claim 6, wherein the photo-diode is pinned.

8. A sensor as claimed in Claim 7, wherein the photo-diode is partially pinned.

9. A method of making a semiconductor image sensor comprising at least one pixel having a

photosensing part, characterized by coating the photosensing part with a coating which performs a dual function.

10. A method as claimed in Claim 9, wherein at least one of the functions of the dual function is a method of fabrication function.

11. A method as claimed in Claim 10, wherein the method of fabrication function is to prevent silicide formation

12. A method as claimed in any of Claims 9 to 11, wherein at least one of the functions of the dual function is an in-use function.

13. A method as claimed in Claim 12, wherein the in-use function is anti-reflection.

14. A method as claimed in any of Claims 9 to 13, further characterized by involving a self-aligning technique.

15. A method as claimed in Claim 14, wherein the photosensing part is a photo-diode and further characterized by pinning the photo-diode.

16. A method as claimed in Claim 15, wherein the photosensing part is a photo-diode and further characterized by partially pinning the photo-diode.